

## NTE3097 and NTE3097-1 Optoisolator Zero Crossing TRIAC Driver

## **Description:**

The NTE3097 and NTE3097–1 are an optoisolator in a 6–Lead DIP type package and contains a gallium arsenide IRED optically coupled to a monolithic silicon detector performing the function of a Zero Voltage Crossing bilateral TRIAC Driver. This device is designed for use with a TRIAC in the interface of logic systems to equipment powered from 240VAC lines such as solid–state relays, industrial controls, motors, solenoids, and consumer appliances, etc.

## Features:

- Simplifies Logic Control of 240VAC Power
- Zero Voltage Crossing
- High Breakdown Voltage: V<sub>DRM</sub> = 400V Min
- High Isolation Voltage: V<sub>ISO</sub> = 7500V Guaranteed
- Small, Economical 6-Lead DIP Package
- dv/dt of 2000V/μs Typ., 1000V/μs Guaranteed

Absolute Maximum Rating: (T <sub>A</sub> = +25°C unless otherwise specified) Infrared Emitting Diode
Reverse Voltage, V <sub>R</sub> 6V
Continuous Forward Current, I <sub>F</sub>
Total Power Dissipation ( $T_A = +25$ °C, Negligible Power in Output Driver), $P_D$
Output Driver
Off-State Output Terminal Voltage, V <sub>DRM</sub>
Peak Repetitive Surge Current (PW = 100μs, 120pps), I <sub>TSM</sub>
Total Power Dissipation ( $T_A = +25^{\circ}C$ ), $P_D$
Total Device
Isolation Surge Voltage (Peak AC Voltage, 60Hz, 1sec Duration, Note 1), V <sub>ISO</sub>
Junction Temperature Range, T <sub>J</sub> 40° to +100°C
Ambient Operating Temperature Range, T <sub>A</sub> –40° to +85°C
Storage Temperature Range, T <sub>stg</sub> 40° to +150°C
Lead Temperature (During Soldering, 10sec), T <sub>L</sub> +260°C

## **<u>Electrical Characteristics:</u>** (T<sub>A</sub> = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Input LED							
Reverse Leakage Current	I <sub>R</sub>	V <sub>R</sub> = 6V	_	0.05	10	μΑ	
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 30mA	-	1.3	1.5	V	
Output Detector (I <sub>F</sub> = 0 unless otherwise specified)							
Leakage With LED OFF	I <sub>DRM1</sub>	Either Direction, V <sub>DRM</sub> = 400V, Note 2	_	2	100	nA	
Peak On-State Voltage	$V_{TM}$	Either Direction, I <sub>TM</sub> = 100mA Peak	_	1.8	3.0	V	
Critical Rate of Rise of Off–State Voltage	dv/dt	Note 4	1000	2000	_	V/μs	
Coupled							
LED Trigger Current, Current Required to Latch Output NTE3097	I <sub>FT</sub>	Main Terminal Voltage = 3V, Note 3	_	_	15	mA	
NTE3097-1			_	_	5	mA	
Holding Current	I <sub>H</sub>	Either Direction	_	100	_	μΑ	
Isolation Voltage	V <sub>ISO</sub>	f = 60Hz, t = 1sec	7500	_	_	VAC(pk)	
Zero Crossing							
Inhibit Voltage	V <sub>IH</sub>	I <sub>F</sub> = 15mA, MT1–MT2 Voltage Above Which Device Will Not Trigger	_	5	20	V	
Leakage in Inhibit State	I <sub>DRM2</sub>	I <sub>F</sub> = 15mA, V <sub>DRM</sub> = 400V, Off–State	_	-	500	μΑ	

- Note 2. Test voltage must be applied within dv/dt rating.
- Note 3. This device is guaranteed to trigger at an  $I_{F1}$  value less than or equal to max.  $I_{FT}$ . Therefore, recommended operating  $I_F$  lies between max.  $I_{FT}$  and absolute max.  $I_F$  (60mA).
- Note 4. This is static dv/dt. Commutating dv/dt is a function of the load-driving thyristor only.

